

## 1. Scope

The present specifications shall apply to a FMB-26.

## 2. Outline

Type	Silicon Schottky Barrier Diode
Structure	Resin Molded      Flammability : UL94V-0 (Equivalent)
Applications	High Frequency Rectification

## 3. Absolute maximum ratings

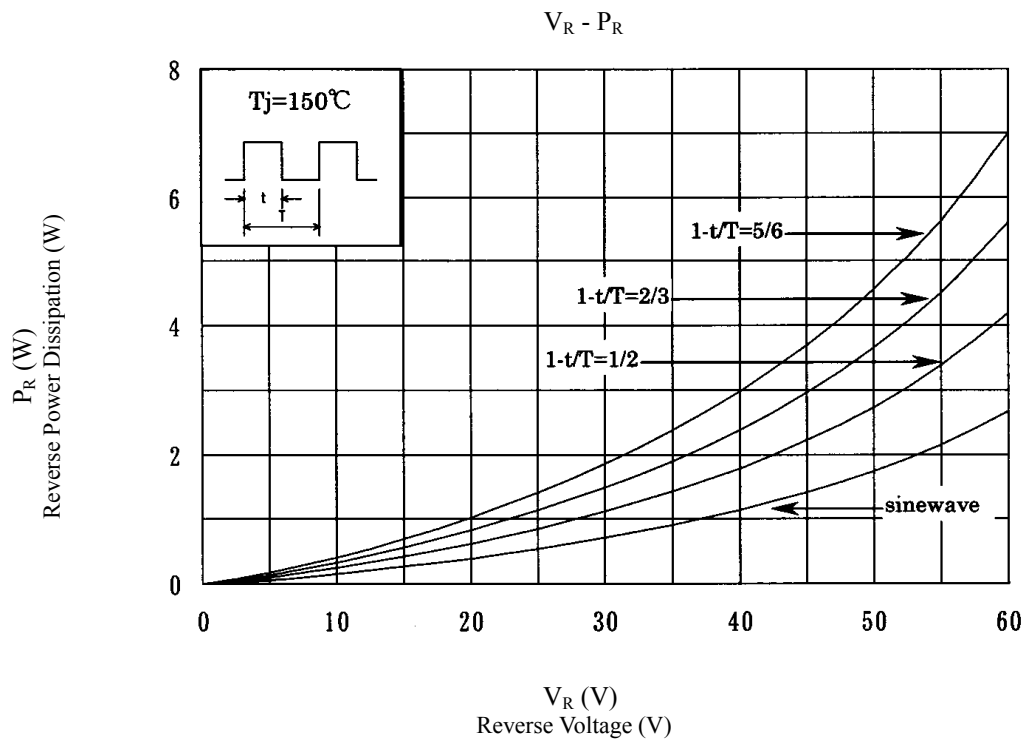
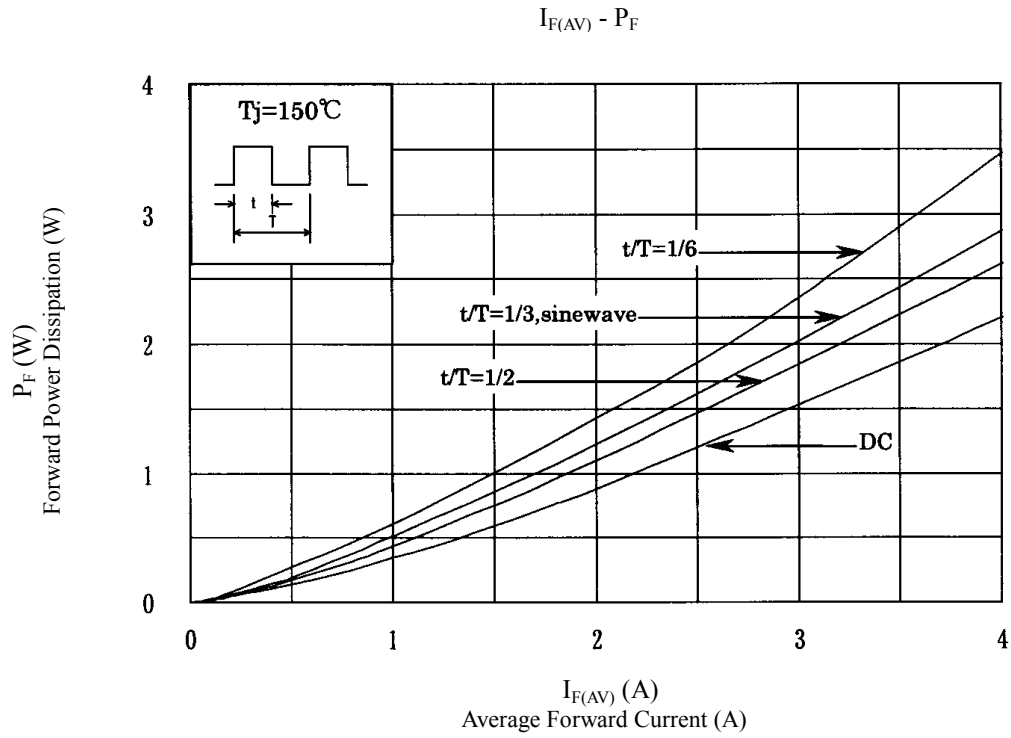
No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	$V_{RSM}$	V	60	
2	Peak Reverse Voltage	$V_{RM}$	V	60	
3	Average Forward Current	$I_{F(AV)}$	A	4.0	$T_c \leq 128^\circ\text{C}$ , Sinewave
4	Peak Surge Forward Current	$I_{FSM}$	A	40	10msec. Half sinewave, one shot
5	$I^2t$ Limiting Value	$I^2t$	$\text{A}^2\text{s}$	8.0	$1\text{msec} \leq t \leq 10\text{msec}$
6	Junction Temperature	$T_j$	$^\circ\text{C}$	-40~+150	
7	Storage Temperature	$T_{stg}$	$^\circ\text{C}$	-40~+150	
8	Dielectric Strength		kV	A.C.1.0	Junction and case (1min)

4. Electrical characteristics( $T_a=25^\circ\text{C}$  , unless otherwise specified)

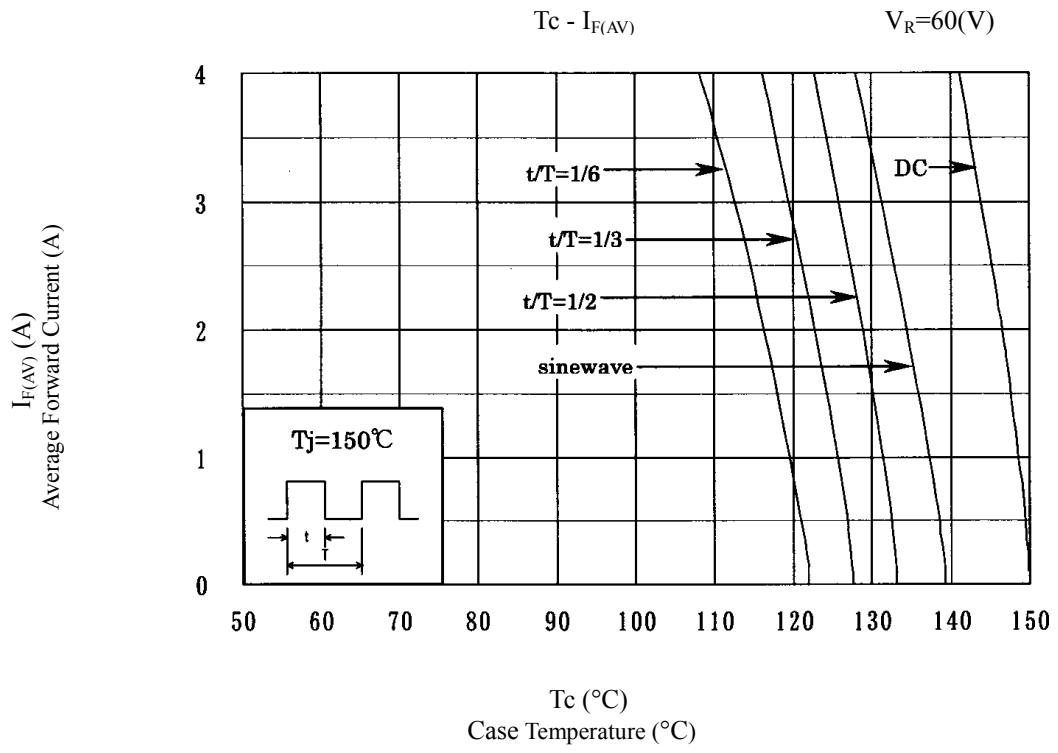
No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	$V_{F1}$	V	0.58 max.	$I_F=1.6\text{A}$
		$V_{F2}$	V	0.62 max.	$I_F=2.0\text{A}$
2	Reverse Leakage Current	$I_R$	mA	2.0 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H \cdot I_{R1}$	mA	20 max.	$V_R=V_{RM}$ , $T_j=125^\circ\text{C}$
		$H \cdot I_{R2}$	mA	70 max.	$V_R=V_{RM}$ , $T_j=150^\circ\text{C}$
4	Thermal Resistance	$R_{th(j-c)}$	$^\circ\text{C}/\text{W}$	4.0 max.	Between Junction and case

No.1,2,&3 show characteristics per one chip.

5. Characteristics

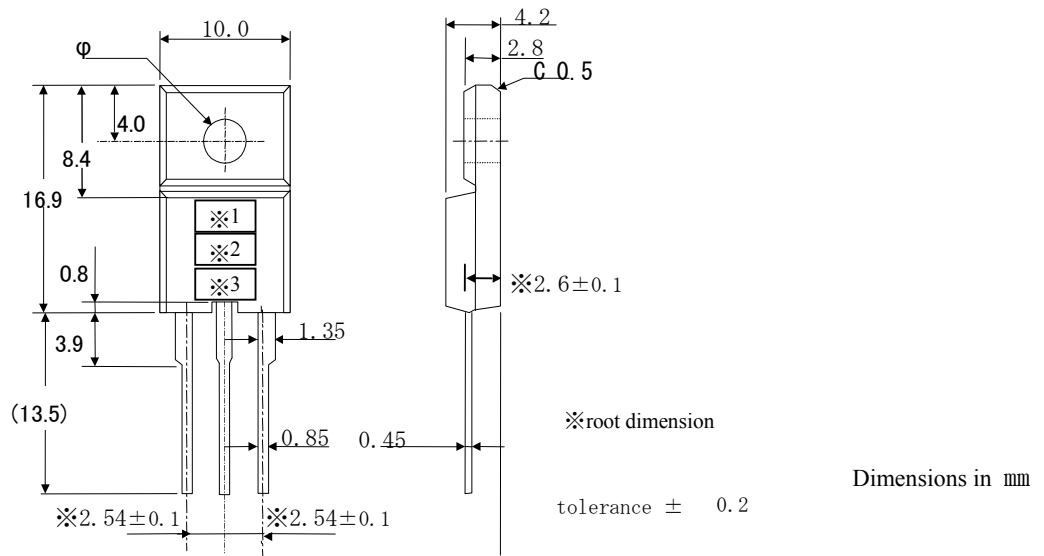


6. Derating



7. Package information

7-1 Package type, physical dimensions and material



7-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

7-3 Marking

Type Name	Marking		
	*1 Type Name	*2 Polarity	*3 Lot number
FMB-26	FMB 26		1st letter: Last digit of year 2nd letter: Month From 1 to 9 for Jan. to Sep., O for Oct., N for Nov., D for Dec. 3rd & 4th letter: Day ex. 4128 (Jan. 28, 2004)